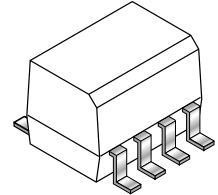


MOCD211-M

DESCRIPTION

The MOCD211-M device consists of two gallium arsenide infrared emitting diodes optically coupled to two monolithic silicon phototransistor detectors, in a surface mountable, small outline plastic package. It is ideally suited for high density applications and eliminates the need for through-the-board mounting.

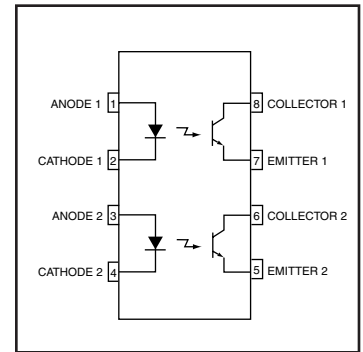


FEATURES

- U.L. Recognized (File #E90700, Volume 2)
- VDE Recognized (File #136616) (add option "V" for VDE approval, i.e, MOCD211V-M)
- Minimum BV_{CEO} of 30 Volts Guaranteed
- Standard SOIC-8 Footprint, with 0.050" Lead Spacing
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- High Input-Output Isolation of 2500 $V_{AC(rms)}$ Guaranteed
- Compact Dual Channel Optocoupler

APPLICATIONS

- Interfacing and coupling systems of different potentials and impedances
- General purpose switching circuits
- Monitor and detection circuits



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless otherwise specified)

Rating	Symbol	Value	Unit
EMITTER			
Forward Current - Continuous	I_F	60	mA
Forward Current - Peak (PW = 100 μs , 120 pps)	$I_F(\text{pk})$	1.0	A
Reverse Voltage	V_R	6.0	V
LED Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	90 0.8	mW mW/ $^\circ\text{C}$
DETECTOR			
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector Voltage	V_{ECO}	7.0	V
Collector Current-Continuous	I_C	150	mA
Detector Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	150 1.76	mW mW/ $^\circ\text{C}$
TOTAL DEVICE			
Input-Output Isolation Voltage ^(1,2,3) (f = 60 Hz, 1 min. Duration)	V_{ISO}	2500	Vac(rms)
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	250 2.94	mW mW/ $^\circ\text{C}$
Ambient Operating Temperature Range	T_A	-40 to +100	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +125	$^\circ\text{C}$

MOCD211-M

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)						
Parameter	Test Conditions	Symbol	Min	Typ**	Max	Unit
EMITTER						
Input Forward Voltage	$I_F = 10\text{ mA}$	V_F	—	1.15	1.5	V
Reverse Leakage Current	$V_R = 6.0\text{ V}$	I_R	—	0.001	100	μA
Capacitance		C	—	18	—	pF
DETECTOR						
Collector-Emitter Dark Current	$V_{CE} = 10\text{ V}, T_A = 25^\circ\text{C}$	I_{CEO1}	—	1.0	50	nA
	$V_{CE} = 10\text{ V}, T_A = 100^\circ\text{C}$	I_{CEO2}	—	1.0	—	μA
Collector-Emitter Breakdown Voltage	$I_C = 100\text{ }\mu\text{A}$	BV_{CEO}	30	100	—	V
Emitter-Collector Breakdown Voltage	$I_E = 100\text{ }\mu\text{A}$	BV_{ECO}	7.0	10	—	V
Collector-Emitter Capacitance	$f = 1.0\text{ MHz}, V_{CE} = 0\text{ V}$	C_{CE}	—	7.0	—	pF
COUPLED						
Current Transfer Ratio ⁽⁴⁾	$I_F = 10\text{ mA}, V_{CE} = 10\text{ V}$	CTR	20	—	—	%
Collector-Emitter Saturation Voltage	$I_C = 2.0\text{ mA}, I_F = 10\text{ mA}$	$V_{CE(sat)}$	—	—	0.4	V
Turn-On Time	$I_C = 2.0\text{ mA}, V_{CC} = 10\text{ V}, R_L = 100\text{ }\Omega$ (fig 6.)	t_{on}	—	7.5	—	μs
Turn-Off Time	$I_C = 2.0\text{ mA}, V_{CC} = 10\text{ V}, R_L = 100\text{ }\Omega$ (fig 6.)	t_{off}	—	5.7	—	μs
Rise Time	$I_C = 2.0\text{ mA}, V_{CC} = 10\text{ V}, R_L = 100\text{ }\Omega$ (fig 6.)	t_r	—	3.2	—	μs
Fall Time	$I_C = 2.0\text{ mA}, V_{CC} = 10\text{ V}, R_L = 100\text{ }\Omega$ (fig 6.)	t_f	—	4.7	—	μs
Isolation Surge Voltage ^(1,2,3)	$f = 60\text{ Hz}, t = 1\text{ min.}$	V_{ISO}	2500	—	—	Vac(rms)
Isolation Resistance ⁽²⁾	$V_{I-O} = 500\text{ V}$	R_{ISO}	10^{11}	—	—	Ω
Isolation Capacitance ⁽²⁾	$V_{I-O} = 0\text{ V}, f = 1\text{ MHz}$	C_{ISO}	—	0.2	—	pF

** Typical values at $T_A = 25^\circ\text{C}$

NOTE:

1. Input-Output Isolation Voltage, V_{ISO} , is an internal device dielectric breakdown rating.
2. For this test, Pins 1, 2, 3 and 4 are common and Pins 5, 6, 7 and 8 are common.
3. V_{ISO} rating of 2500 V_{AC(rms)} for $t = 1\text{ min.}$ is equivalent to a rating of 3,000 V_{AC(rms)} for $t = 1\text{ sec.}$
4. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.

Fig. 1 LED Forward Voltage vs. Forward Current

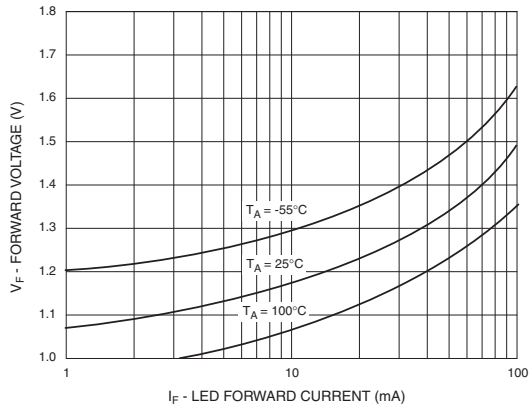


Fig. 2 Output Current vs. Input Current

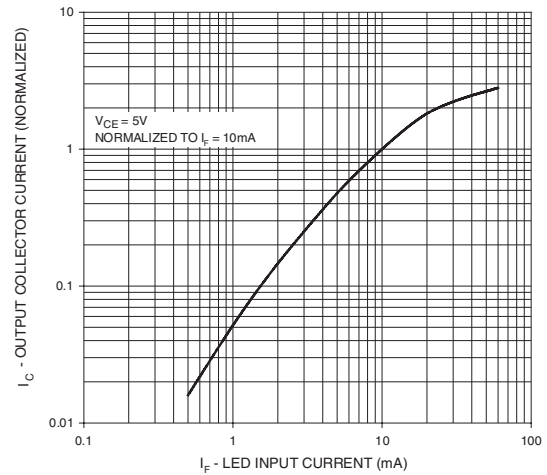


Fig. 3 Output Current vs. Ambient Temperature

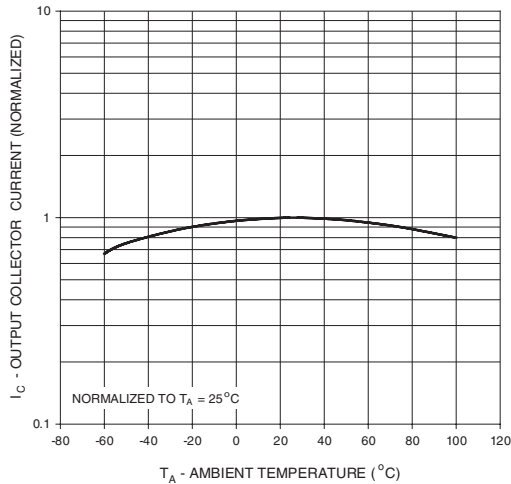


Fig. 4 Output Current vs. Collector - Emitter Voltage

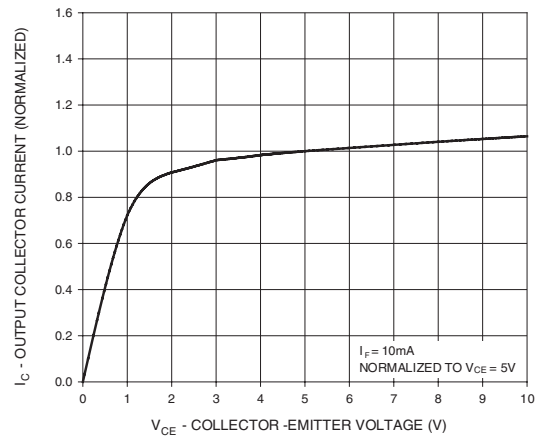
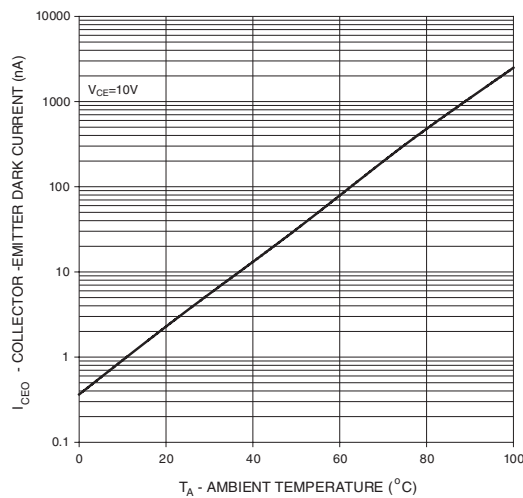


Fig. 5 Dark Current vs. Ambient Temperature



MOCD211-M

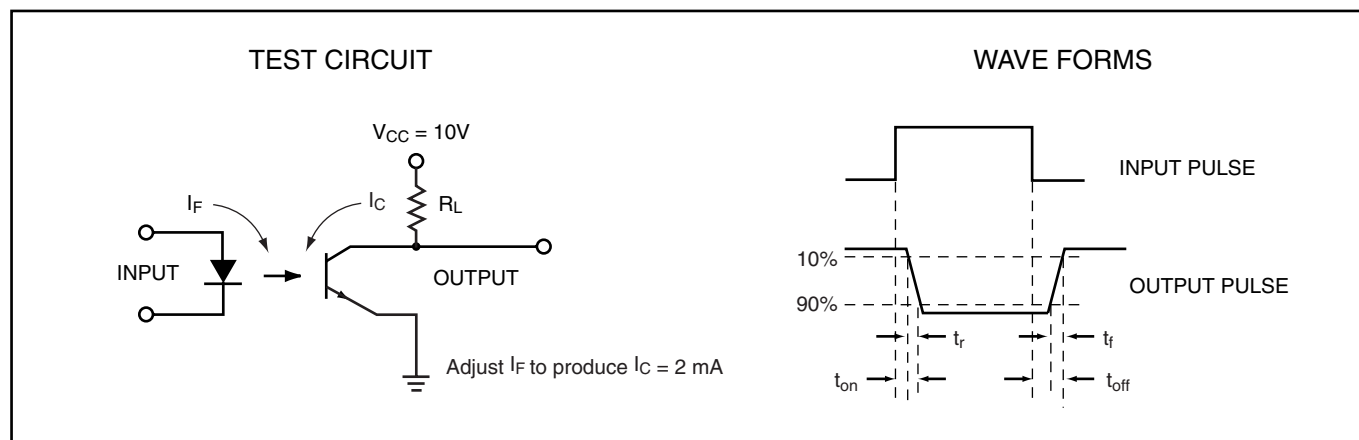
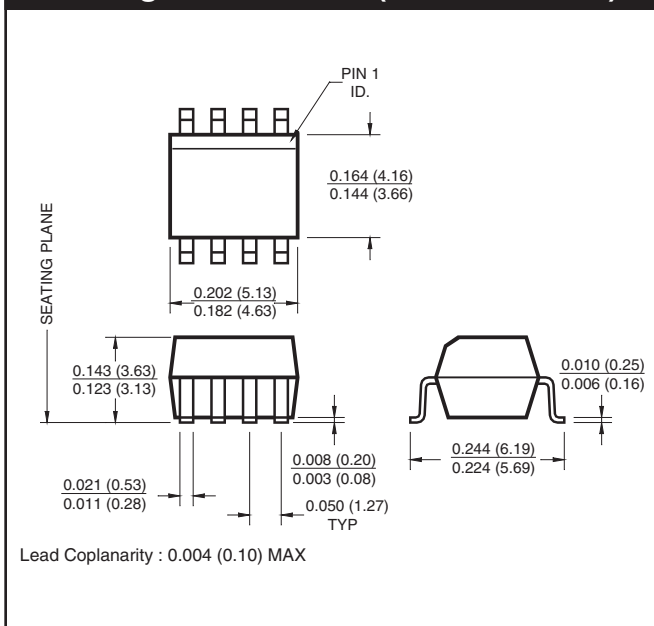


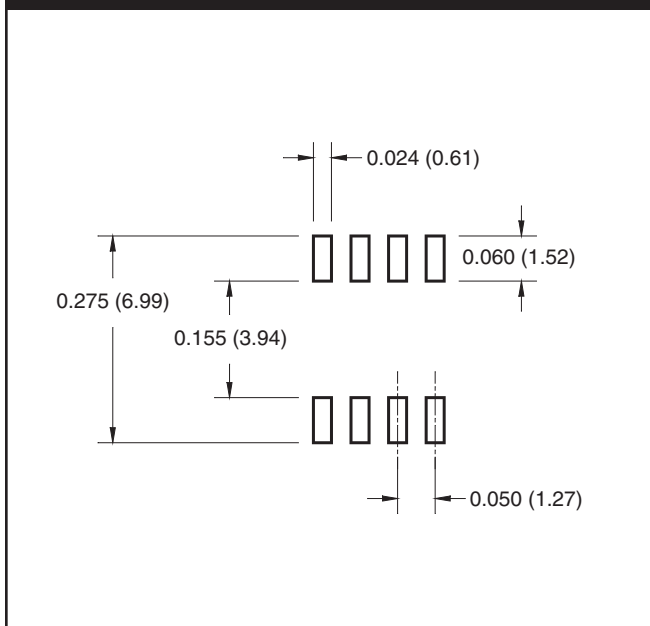
Figure 6. Switching Time Test Circuit and Waveforms

MOCD211-M

Package Dimensions (Surface Mount)



8-Pin Small Outline

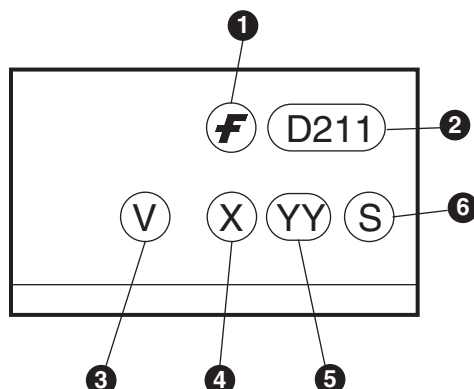


MOCD211-M

ORDERING INFORMATION

Option	Order Entry Identifier	Description
V	V	VDE 0884
R1	R1	Tape and reel (500 units per reel)
R1V	R1V	VDE 0884, Tape and reel (500 units per reel)
R2	R2	Tape and reel (2500 units per reel)
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)

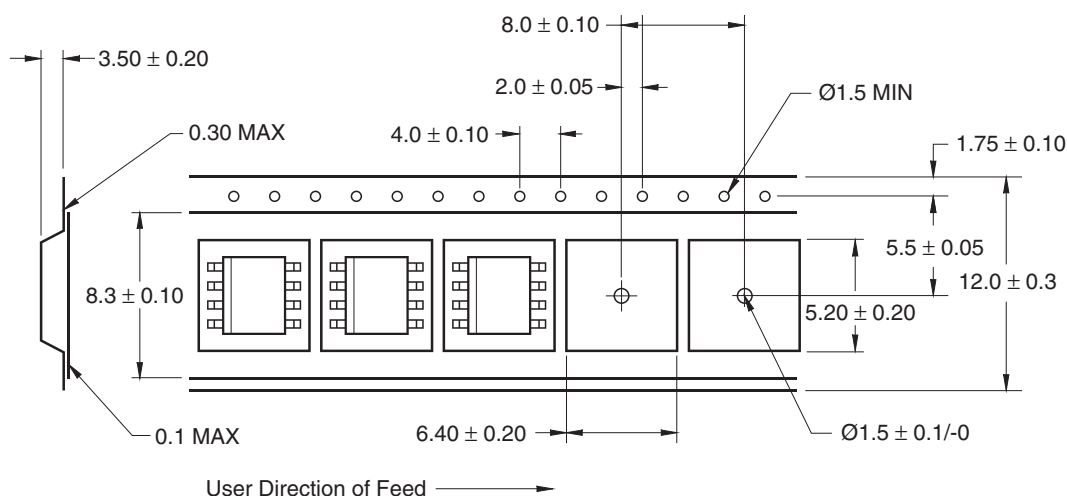
MARKING INFORMATION



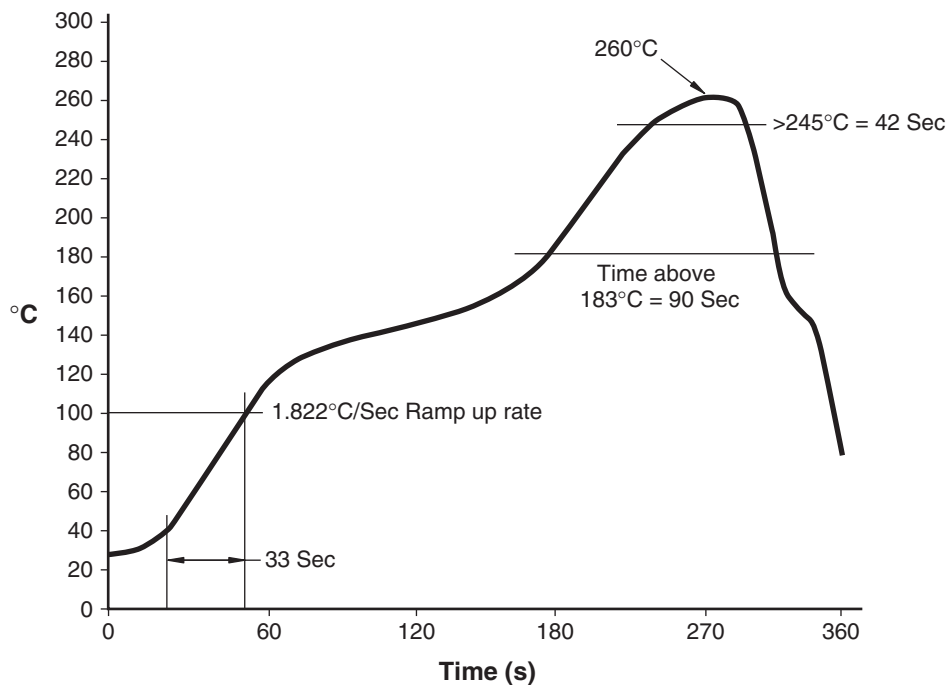
Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '3'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

MOCD211-M

Carrier Tape Specifications



Reflow Profile



DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.